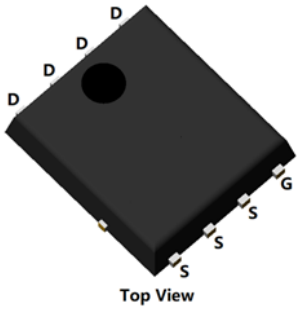
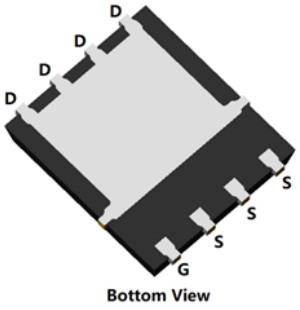
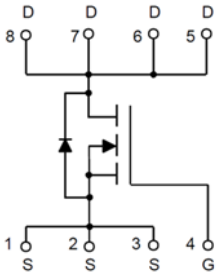
N-Channel Enhancement Mode Field Effect Transistor





PDFN5060-8L



Product Summary

- V_{DS} 120V
- I_D 88A
- $R_{DS(ON)}$(at V_{GS}=10V) ＜7.6mohm
- $R_{DS(ON)}$(at V_{GS}=4.5V) ＜9.6mohm
- 100% EAS Tested
- 100% ▽VDS Tested

General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

■ Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	120	V
Gate-source Voltage		V_{GS}	±20	V
Drain Current	T_C=25℃	I_D	88	A
	Tc=100℃		56	
Pulsed Drain Current [A]		I_{DM}	352	A
Avalanche energy [B]		EAS	400	mJ
Total Power Dissipation [C]	Tc=25℃	P_D	120	W
	Tc=100℃		48	
Junction and Storage Temperature Range		T_J ,T_{STG}	-55～+150	℃

■Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient [D]	t≤10S	$R_{\theta JA}$	15	20	℃/W
Thermal Resistance Junction-to-Ambient [D]	Steady-State		40	50	
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	0.84	1.04	

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
G88G12A	F1	G88G12A	5000	10000	100000	13“ reel

■ Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	120	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=120V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±20V, V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	1.0	2.0	3.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A	-	6.4	7.6	mΩ
		V_{GS}=4.5V, I_D=20A	-	7.6	9.6	mΩ
Diode Forward Voltage	V_{SD}	I_S=20A,V_{GS}=0V	-	-	1.3	V
Forward Transconductance	g_{FS}	V_{DS}=5V, I_D=20A	-	80	-	S
Gate resistance	R_G	f=1MHz	-	0.9	-	Ω
Maximum Body-Diode Continuous Current	I_S		-	-	88	A
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=50V,V_{GS}=0V,f=1MHZ	-	4619	-	pF
Output Capacitance	C_{oss}		-	924	-	
Reverse Transfer Capacitance	C_{rss}		-	28	-	
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=10V,V_{DS}=50V,I_D=20A	-	72.0	-	nC
Gate-Source Charge	Q_{gs}		-	19.5	-	
Gate-Drain Charge	Q_{gd}		-	8.2	-	
Reverse Recovery Chrage	Q_{rr}	I_F=20A, di/dt=100A/us	-	195	-	
Reverse Recovery Time	t_{rr}		-	86	-	ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=10V,V_{DD}=50V,I_D=20A R_{GEN}=2.2Ω	-	19	-	
Turn-on Rise Time	t_r		-	36	-	
Turn-off Delay Time	$t_{D(off)}$		-	45	-	
Turn-off fall Time	t_f		-	45	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T_J=25℃, V_{DD}=50V, V_G=10V, R_G=25Ω, L=2mH,I_{AS}=20A

C. P_d is based on max. junction temperature, using junction-case thermal resistance.

D. The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation PDSM is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

■ Typical Performance Characteristics

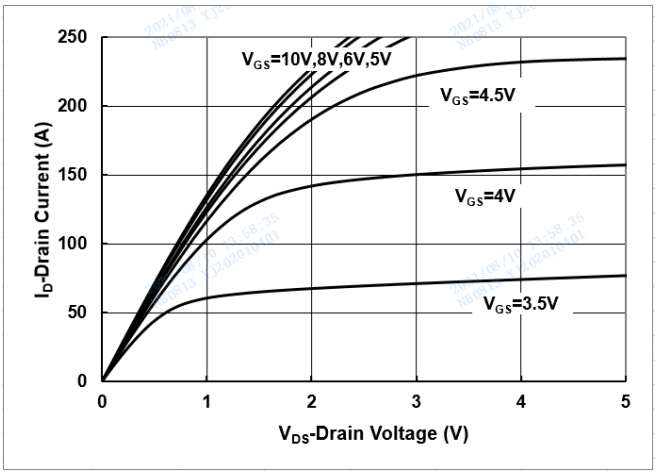


Figure1. Output Characteristics

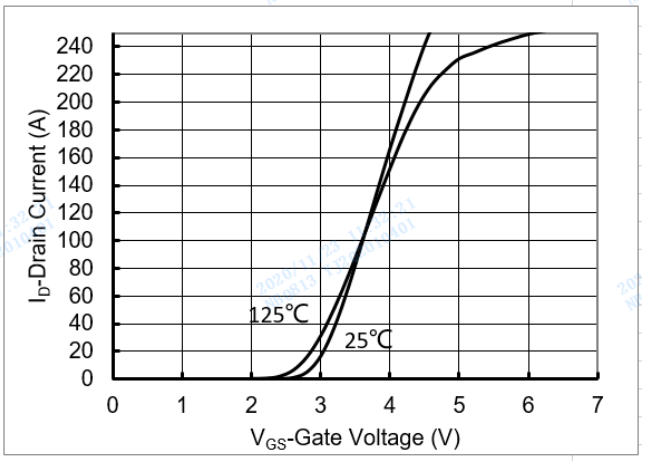


Figure2. Transfer Characteristics

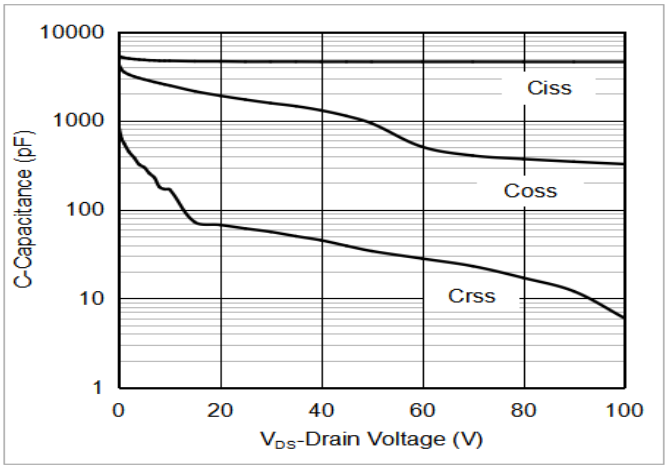


Figure3. Capacitance Characteristics

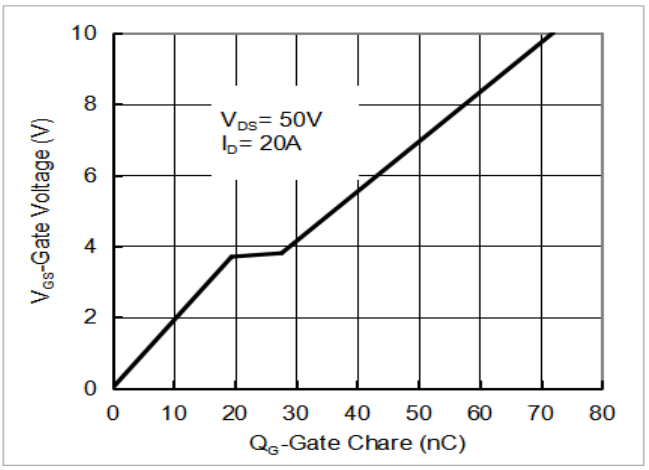


Figure4. Gate Charge

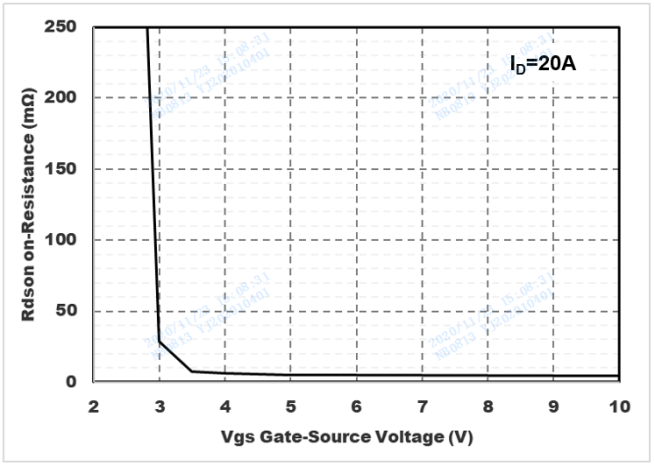


Figure5. : On-Resistance vs. Gate to Source Voltage

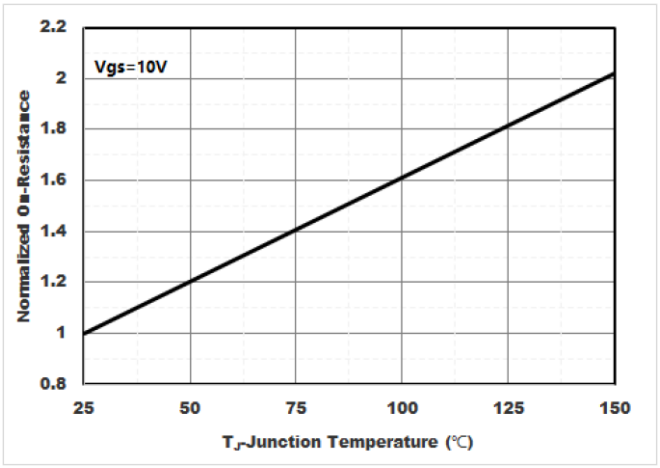


Figure6.Normalized On-Resistance

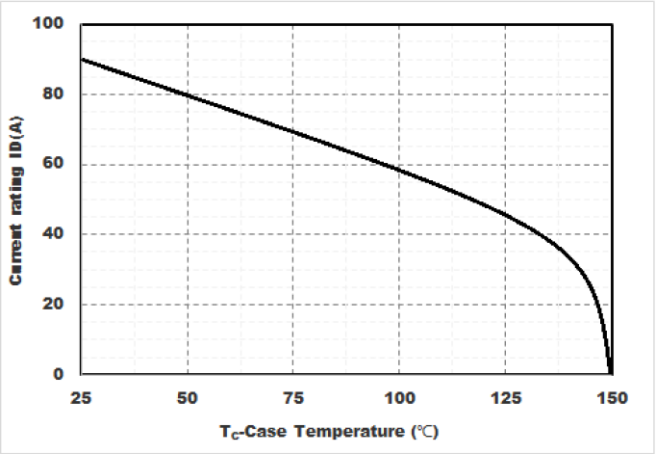


Figure7. Drain current

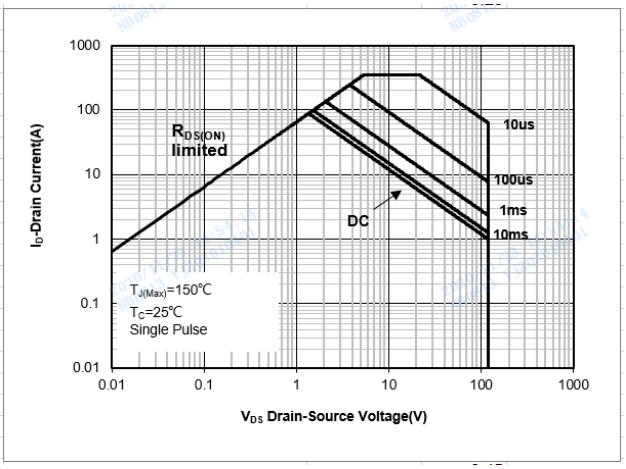


Figure8.Safe Operation Area

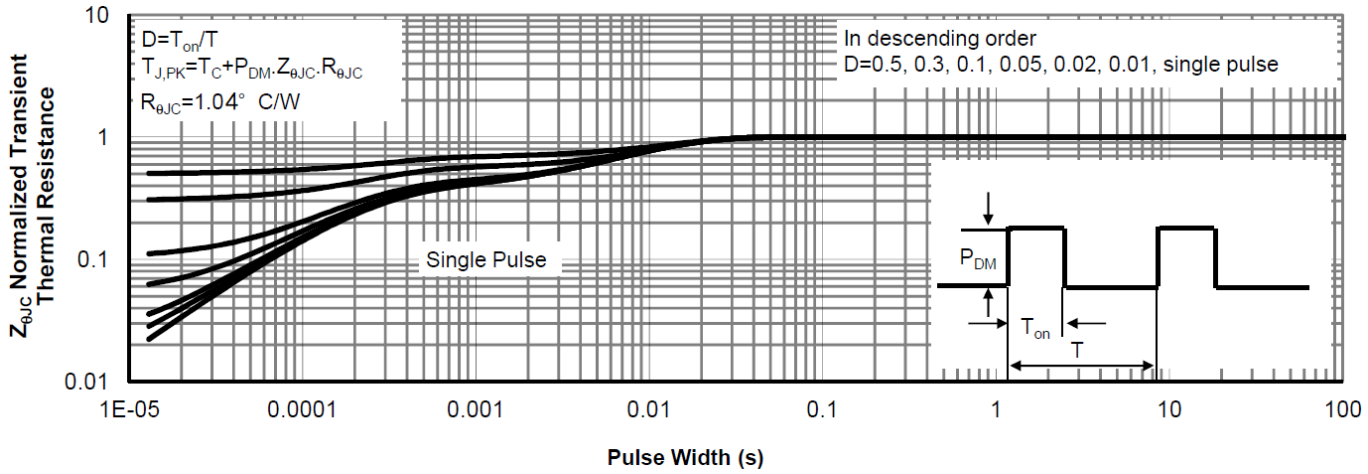
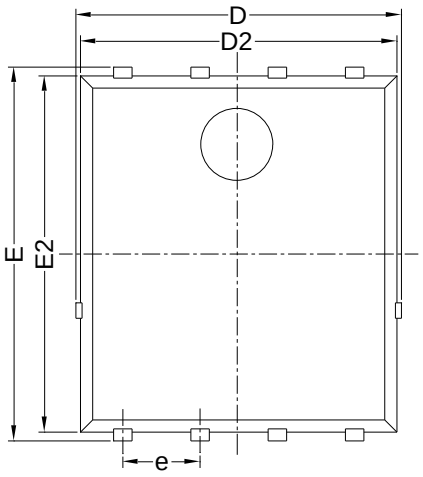
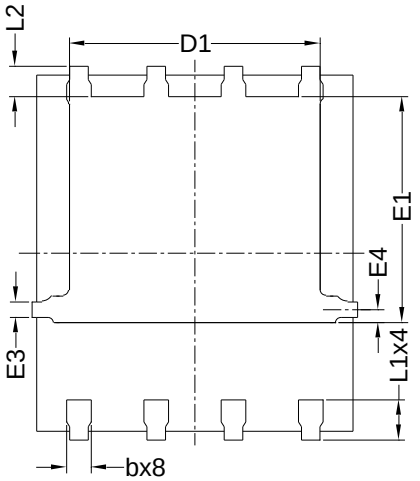


Figure9. Normalized Maximum Transient thermal impedance

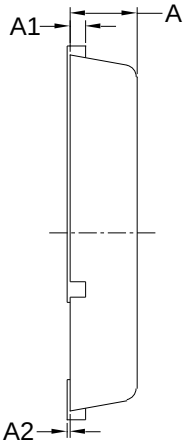
■ PDFN5060-8L-B-1.1MM Package information



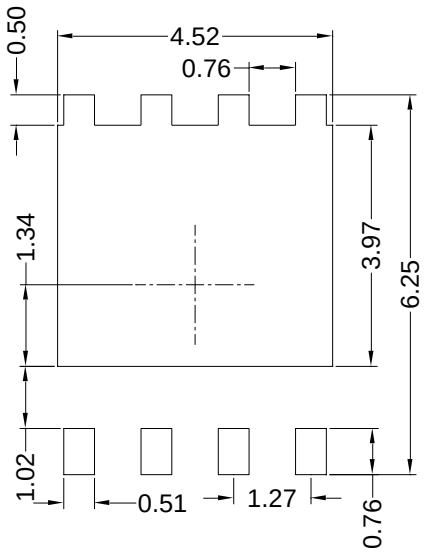
Top View
正面视图



Bottom View
背面视图



Side View
侧面视图



Suggested Solder Pad Layout
Top View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1		0.254 BSC	
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3		0.254 REF	
E4		0.21 REF	
L1	0.56	0.66	0.76
L2		0.50 BSC	
b	0.31	0.41	0.51
e		1.27 BSC	

Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.10mm.
3.The pad layout is for reference purposes only.

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